



SCHOTTKY BARRIER DIODE

●Applications

Low current rectification and high speed switching

●Features

Extremelysmall surface mounting type. (SC-79/SOD523)

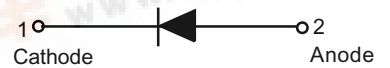
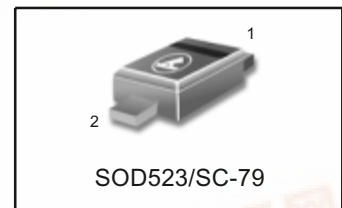
$I_o=200\text{mA}$ guaranteed despite the size.

Low V_F . ($V_F=0.40\text{V}$ Typ. At 200mA)

●Construction

silicon epitaxial planar

LRB521S-30T1



MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_o	200	mA
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{slg}	-40~+125	$^\circ\text{C}$

*60Hz for 1 ∞

DEVICE MARKING

LRB521S-30T1=5M

ELECTRICAL CHARACTERISTICS($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.50	V	$I_F=200\text{mA}$
Reverse current	I_R	-	-	30	μA	$V_R=10\text{V}$



LRB521S-30T1

Electrical characteristic curves(Ta=25°C)

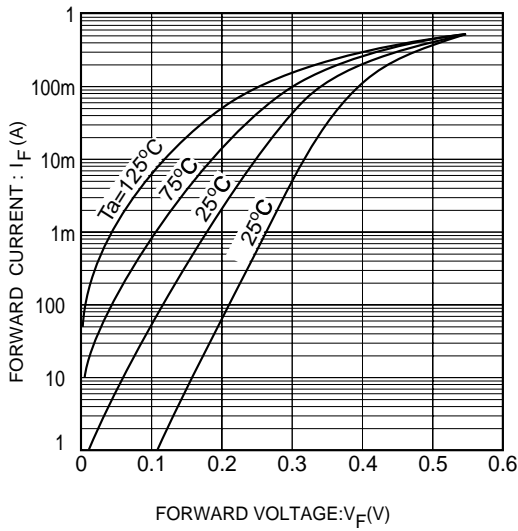


Fig. 1 Forward characteristics

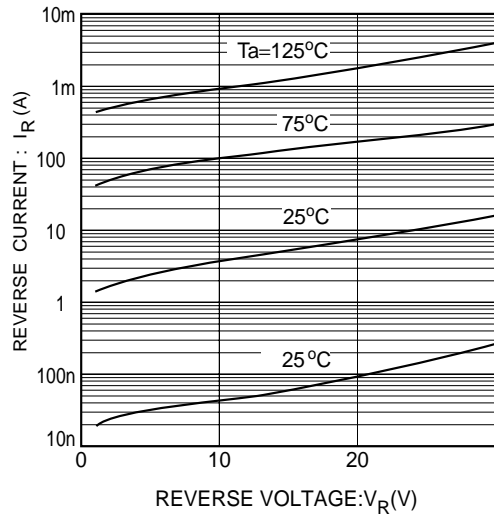


Fig. 2 Reverse characteristics

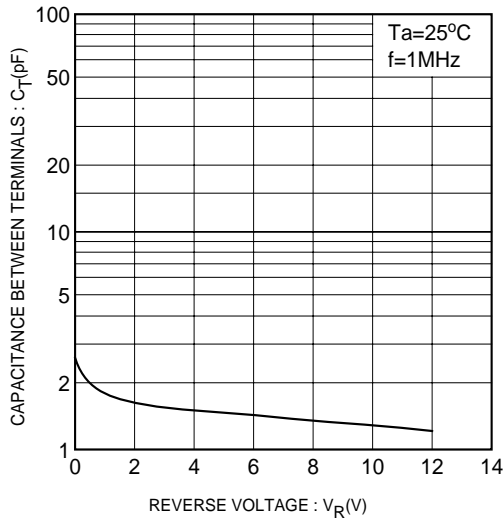


Fig. 3 Capacitance between terminals characteristics

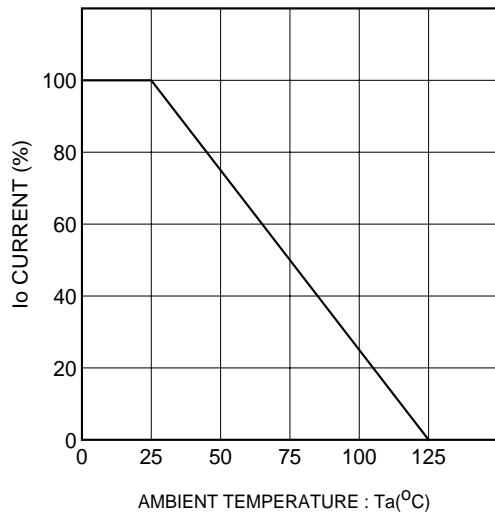
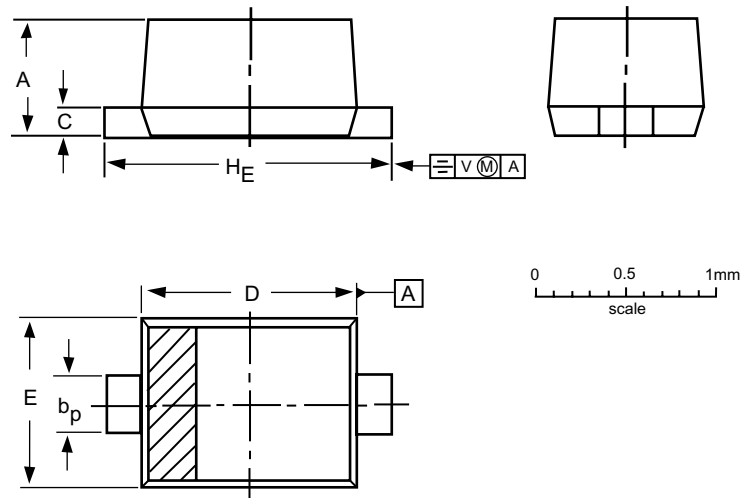


Fig. 4 Derating curve (mounting on glass epoxy PCBs)



LRB521S-30T1

SC-79/SOD-523

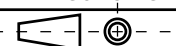


DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	H _E	V
mm	0.7	0.35	0.2	1.3	0.9	1.7	0.15
	0.5	0.25	0.1	1.1	0.7	1.5	

Note

- The marking bar indicates the cathode.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOD523			SC-79		98-11-25

